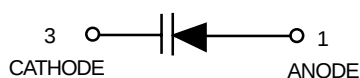


Silicon Pin Diode

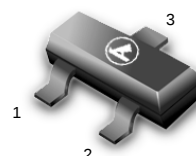
This device is designed primarily for VHF band switching applications but is also suitable for use in general-purpose switching circuits. Supplied in a surface Mount package.

- Rugged Pin Structure Coupled with Wirebond Construction for Optimum Reliability
- Low Capacitance—0.7pF Typ at VR=20Vdc
- Very Low Series Resistance at 100MHz—0.34Ohms(Typ)@IF=10mAdc



MMBV3401LT1

**SILICON PIN
SWITCHING DIODE**



**CASE 318-08, STYLE 6
SOT- 23 (TO-236AB)**

MAXIMUM RATINGS(EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	20	Vdc
Forward power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		2.0	mW/ $^\circ\text{C}$
Junction Temperature	T_J	+125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBV3401LT1=4D

ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R=10\mu\text{Adc}$)	$V_{(BR)R}$	35	—	—	Vdc
Diode Capacitance ($V_R=20\text{ Vdc}$)	C_T	—	—	1.0	pF
Series Resistance(figure5) ($I_F=10\text{mAdc}$, $f=100\text{MHz}$)	R_S	—	—	0.7	Ω
Reverse Voltage Leakage Current ($V_R=15\text{Vdc}$)	I_R	—	—	0.1	μAdc

MMBV3401LT1

TYPICAL CHARACTERISTICS

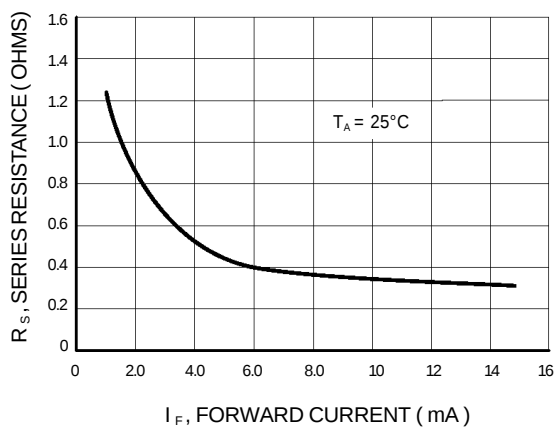


Figure 1. Series Resistance

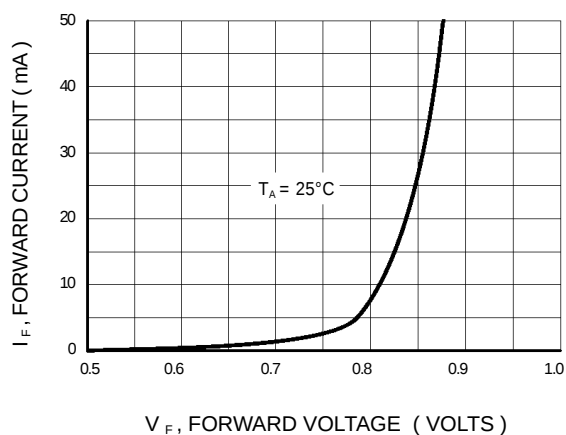


Figure 2. Forward Voltage

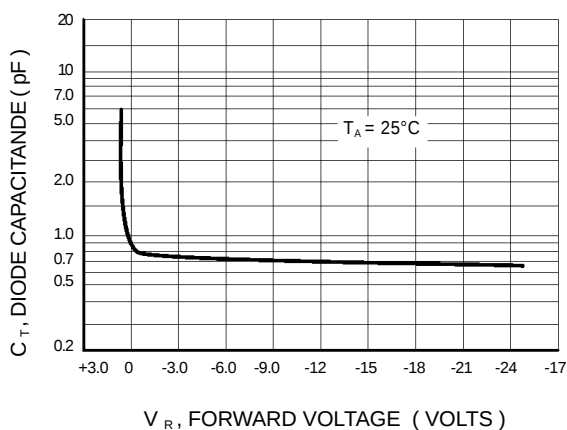


Figure 3. Diode Capacitance

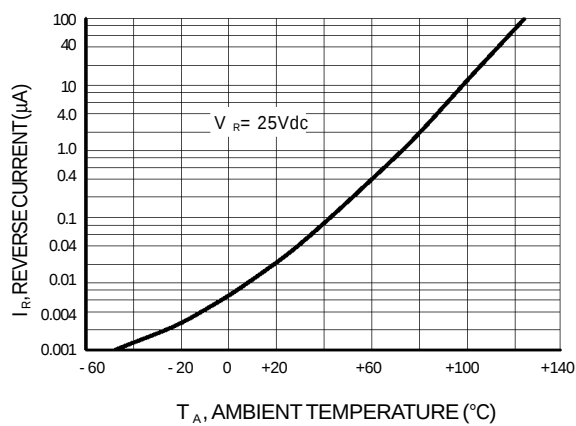


Figure 4. Leakage Current